

AMENDMENTS TO THE SPECIFICATION

At page 1, just before "Background of the Invention," please insert the following new paragraph:

This application is a continuation of U.S. patent application 10/100,450, filed March 14, 2002, ^{now Patent No. 6,849,868} entitled "METHODS AND APPARATUS FOR RESISTANCE VARIABLE MATERIAL CELLS," which is hereby incorporated by reference herein in its entirety.

Please replace the appropriate paragraphs of the specification with the respective amended paragraphs presented below:

[0006] In addition, Mitkova, et al., found that glasses that fall within the stoichiometry range defined by region II of Figure 1 of the Mitkova reference do not form silver selenide when doped with silver (Ag). For example, a rigid glass, such as germanium selenide ($\text{Ge}_{0.40}\text{Se}_{0.60}$) will not form silver selenide when photodoped with silver (Ag) and, as a result, does not function as a memory switch.

[0007] The presence of silver selenide in a $\text{Ge}_x\text{Se}_{1-x}$ glass photodoped with silver (Ag) allows the glass to be used as a memory switch. Glasses used for silver (Ag) incorporation via photodoping are floppy and switch more slowly electrically, and with worse memory retention, than glasses that are rigid. Preferred rigid glasses, e.g., $\text{Ge}_{0.40}\text{Se}_{0.60}$, do not form silver selenide when photodoped with silver (Ag). However,